
VE320 – Summer 2024

Introduction to Semiconductor Devices

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Chapter 11 Metal-Oxide-Semiconductor Field Effect
Transistors: More Concepts



VE320 Yaping Dan

Outline

Nonideal Effects:

11.1 Channel length modulation

11.2 Conductance and transconductance

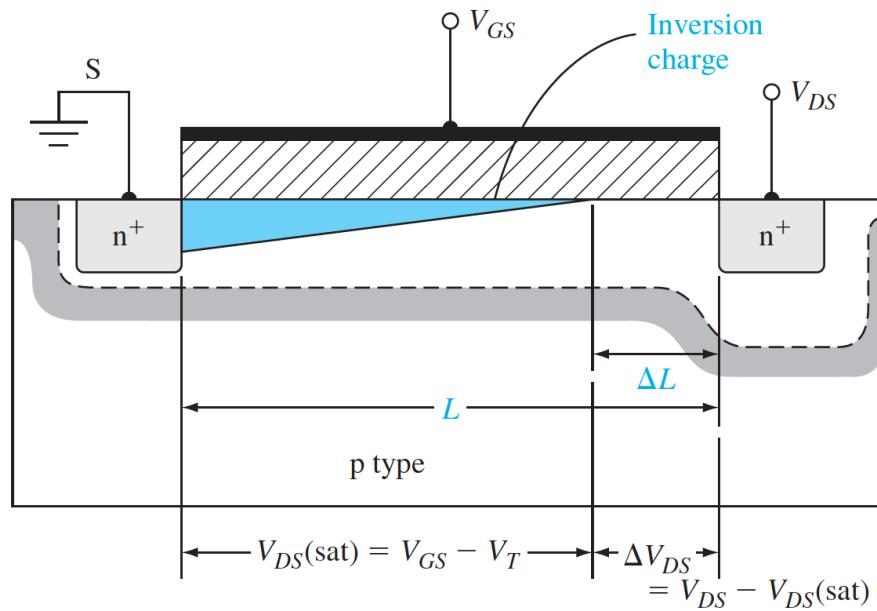
11.3 Subthreshold conduction

11.4 Velocity Saturation

11.5 Short Channel Effect



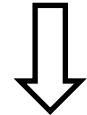
11.1 Channel length modulation



$$I'_D = \frac{k'_n}{2} \cdot \frac{W}{L} \cdot [(V_{GS} - V_T)^2 (1 + \lambda V_{DS})]$$

11.1 Channel length modulation

$$I_D = \begin{cases} 0 & V_{GS} - V_T < 0 \\ \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_T)^2 & 0 \leq V_{GS} - V_T < V_{DS} \\ \mu_n C_{ox} \frac{W}{L} [(V_{GS} - V_T) V_{DS} - \frac{1}{2} V_{DS}^2] & V_{GS} - V_T \geq V_{DS} \end{cases}$$



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Check your understanding

Problem Example 1

Consider an n-channel silicon MOSFET. The parameters are $k'_n = 75 \mu\text{A/V}^2$, $W/L = 10$, and $V_T = 0.35 \text{ V}$. The applied drain-to-source voltage is $V_{DS} = 1.5 \text{ V}$.

(a) For $V_{GS} = 0.8 \text{ V}$, find (i) the ideal drain current, (ii) the drain current if $\lambda = 0.02 \text{ V}^{-1}$, and (iii) the output resistance for $\lambda = 0.02 \text{ V}^{-1}$. (b) Repeat part (a) for $V_{GS} = 1.25 \text{ V}$.



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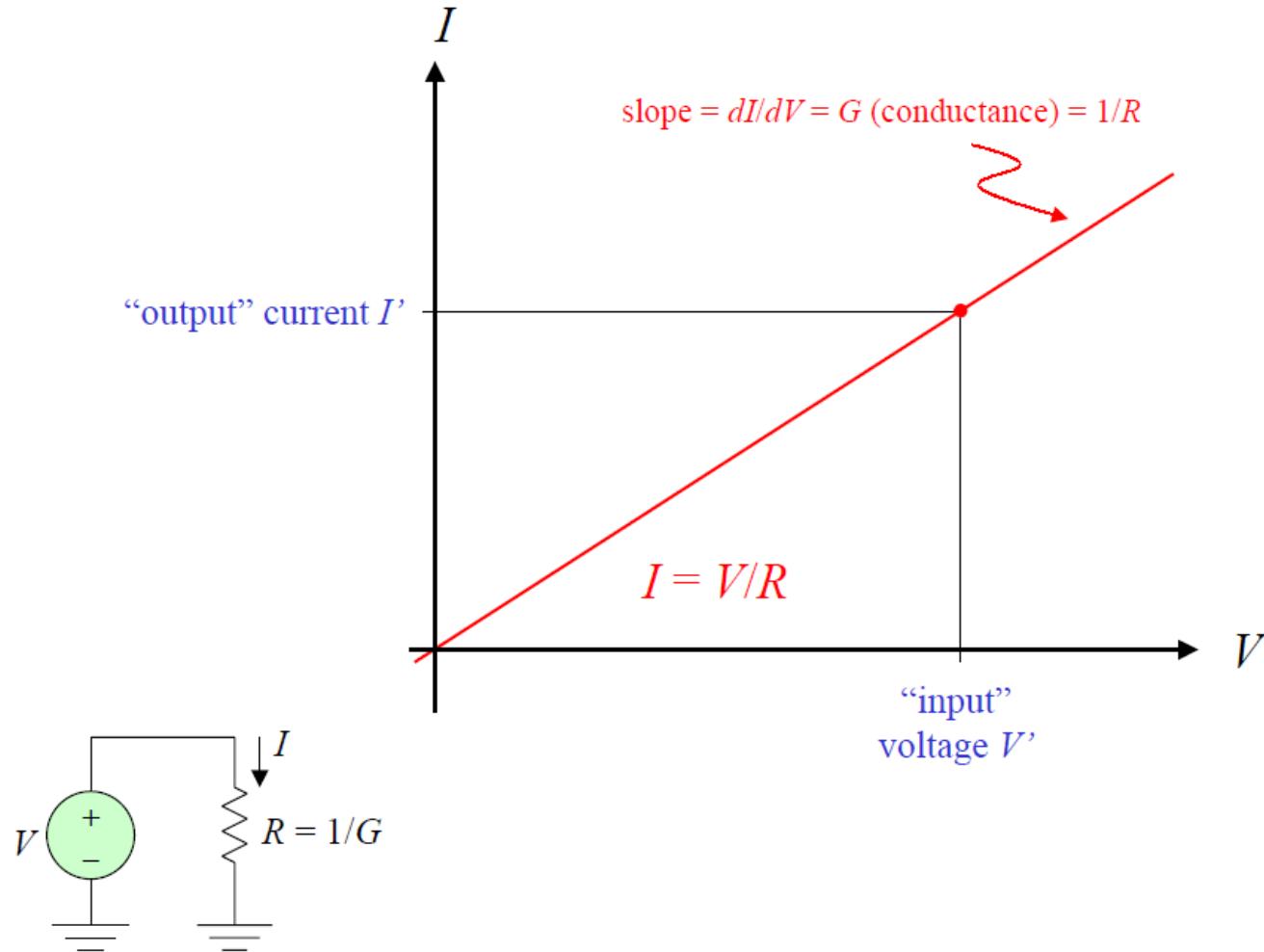
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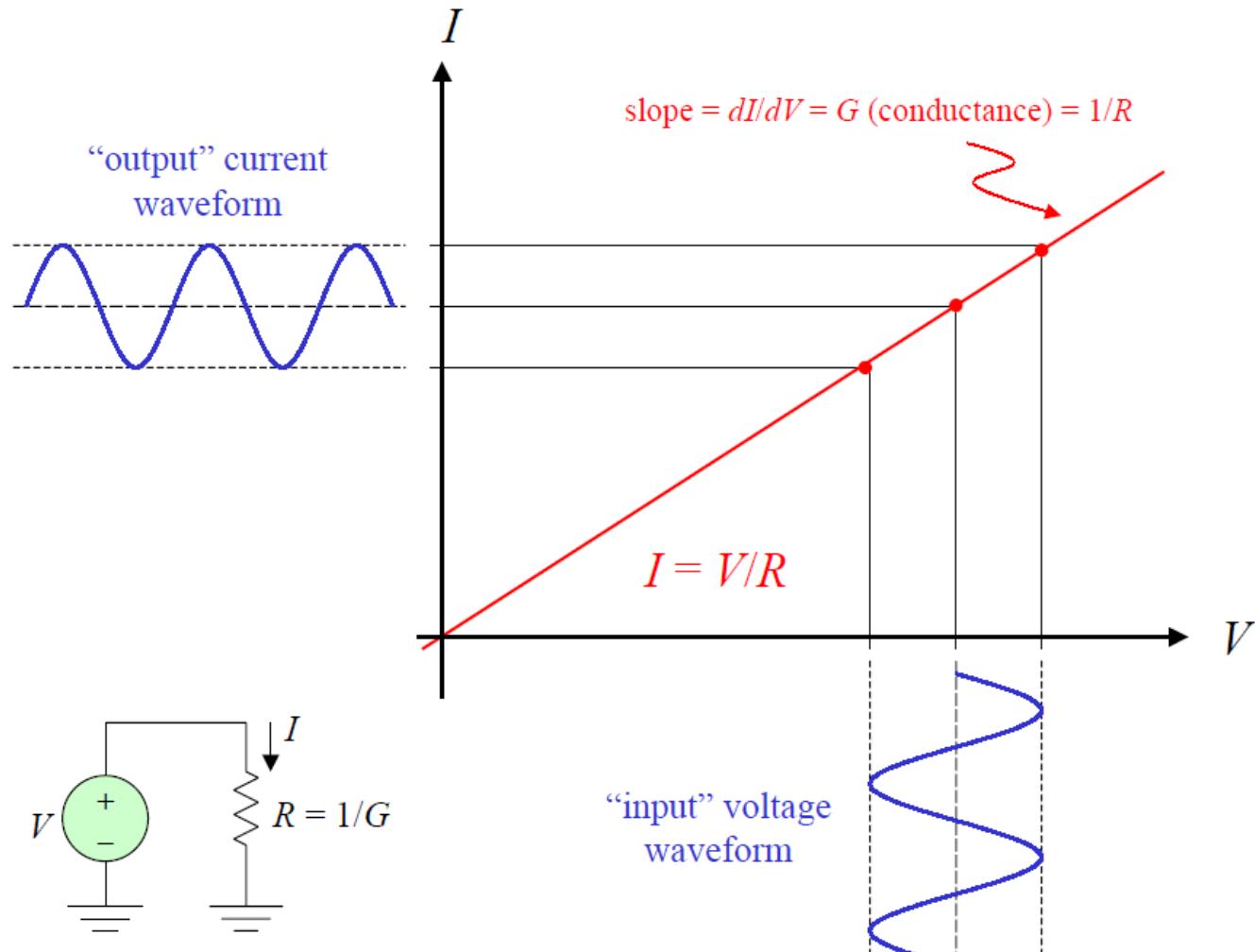
11.5 Short Channel Effect



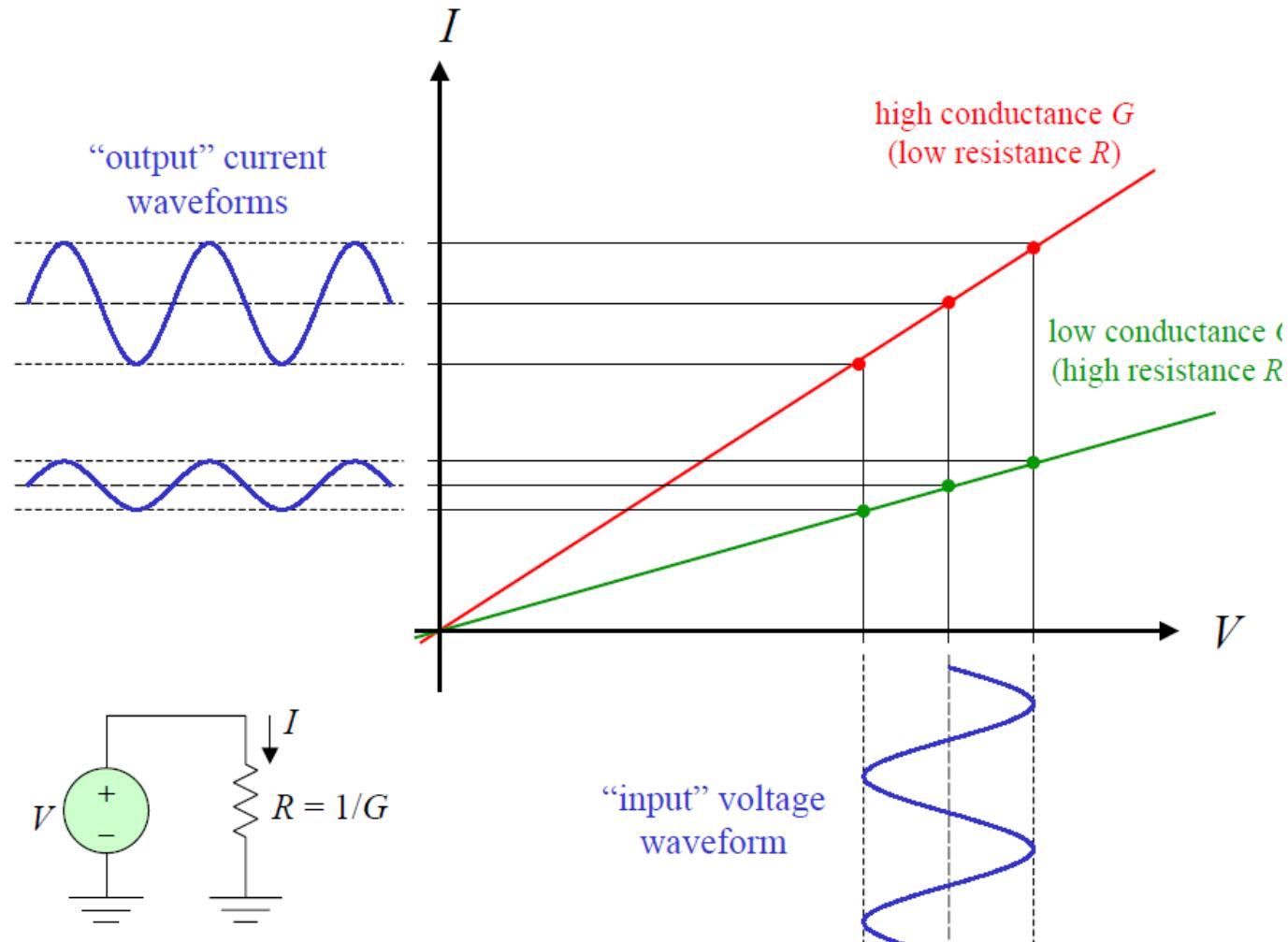
11.2 conductance and transconductance



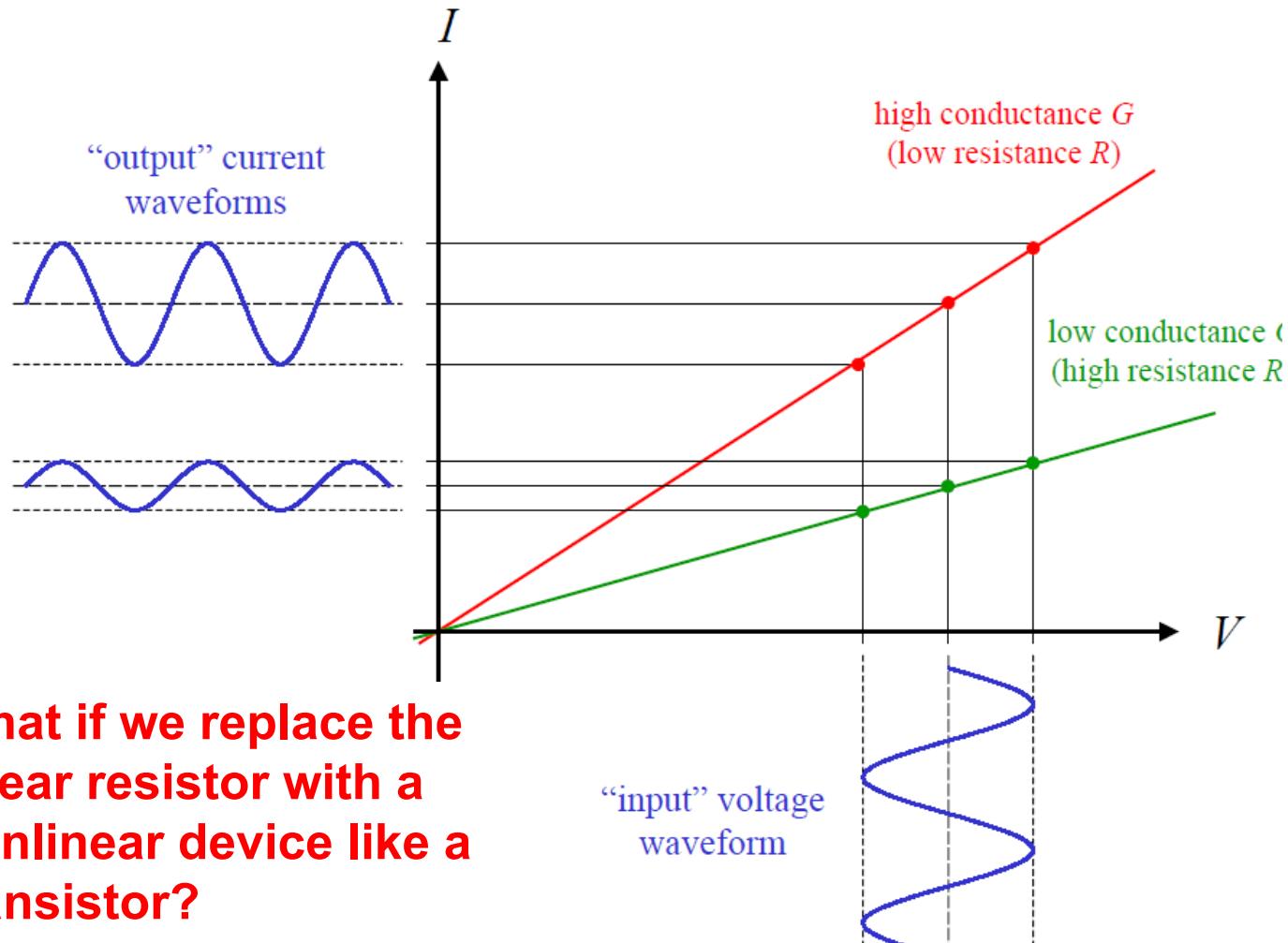
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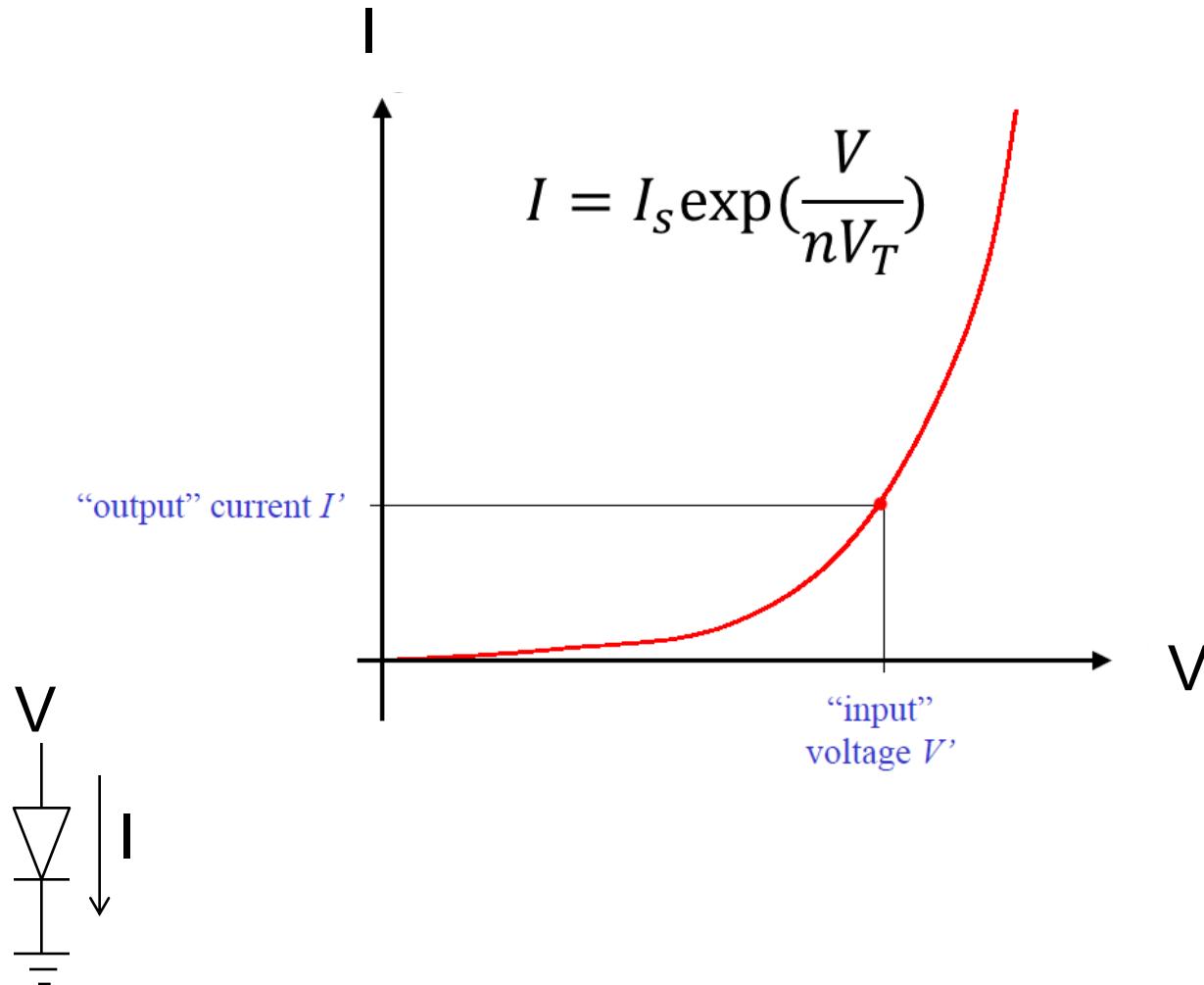
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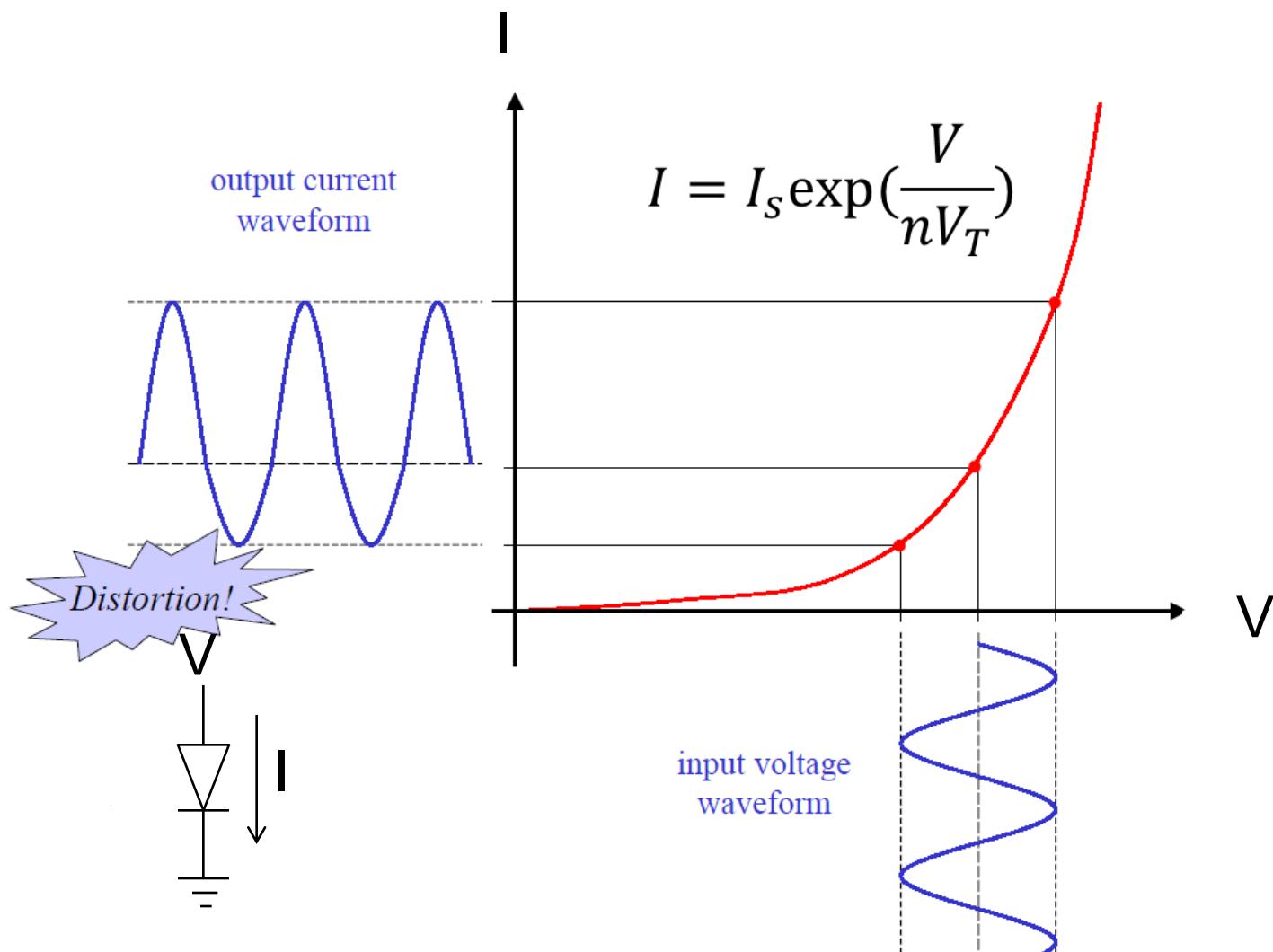
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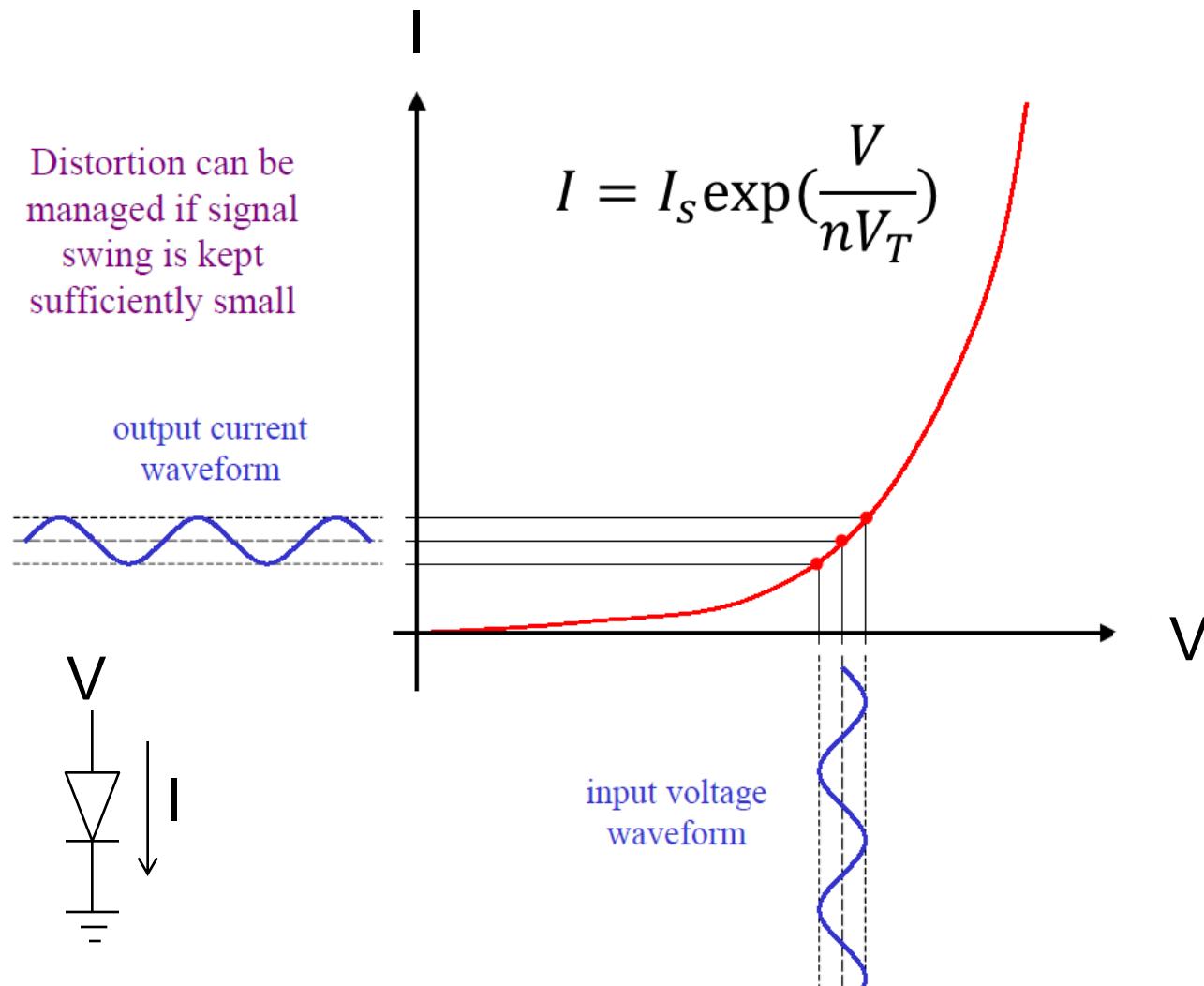
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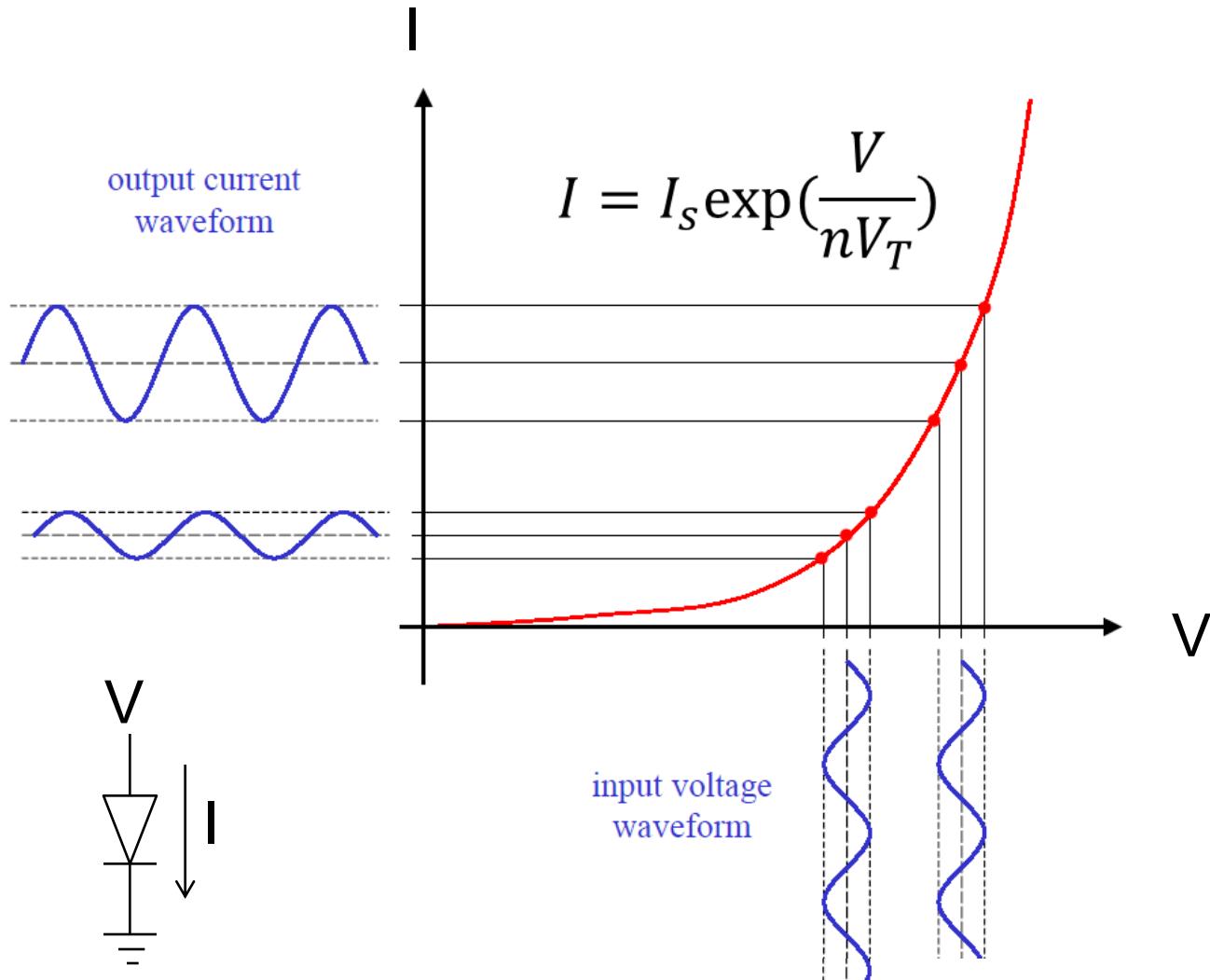
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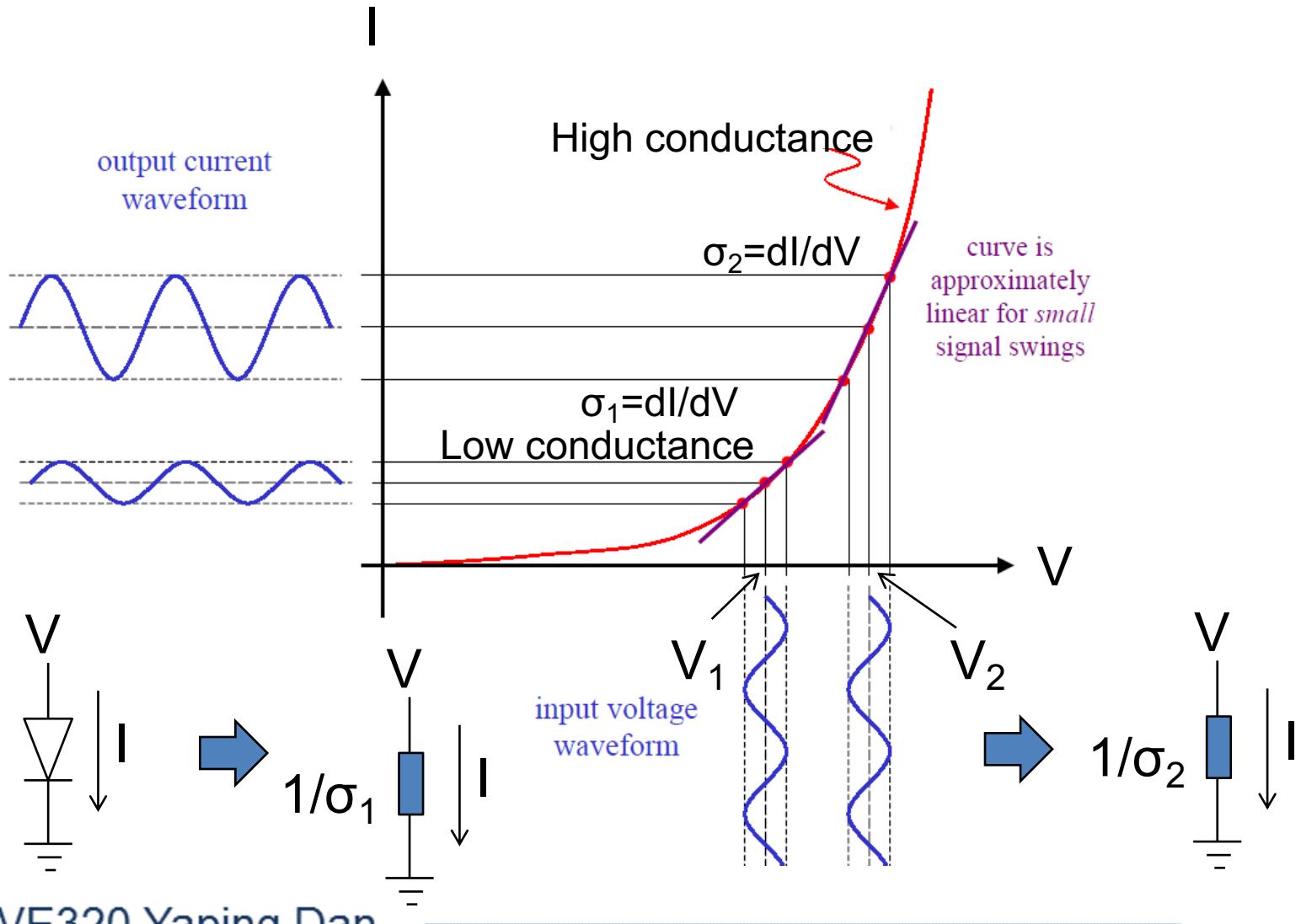
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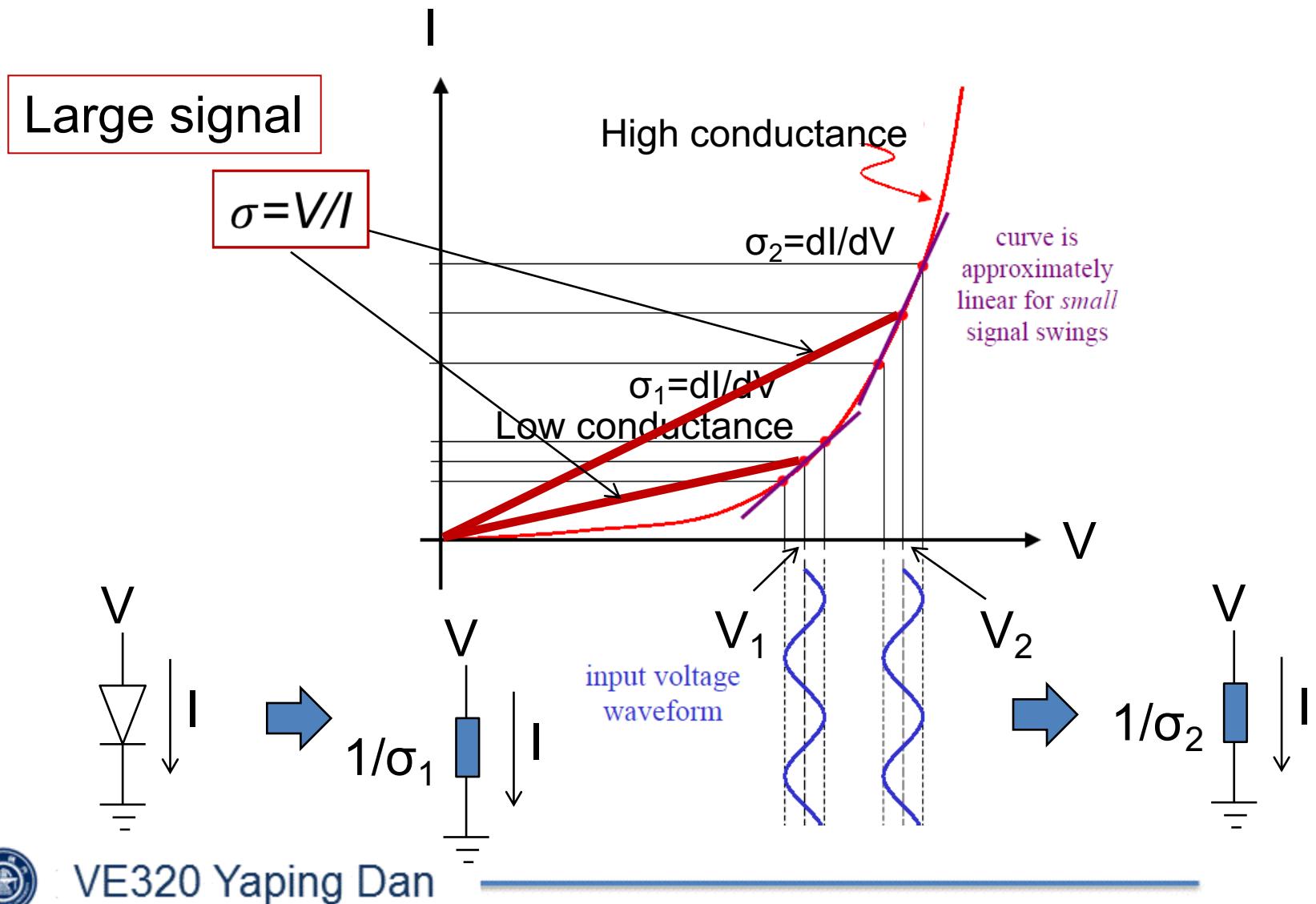
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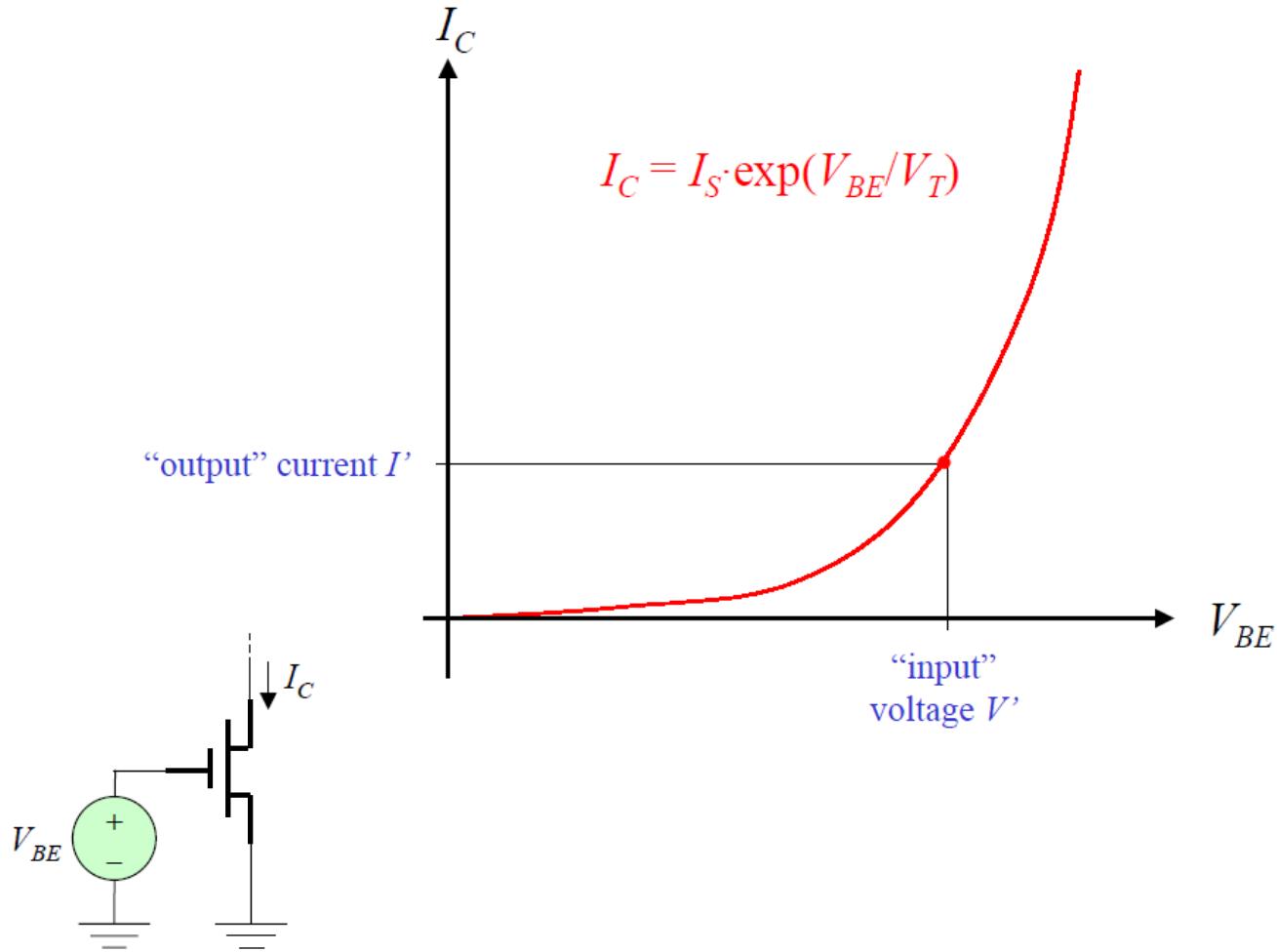
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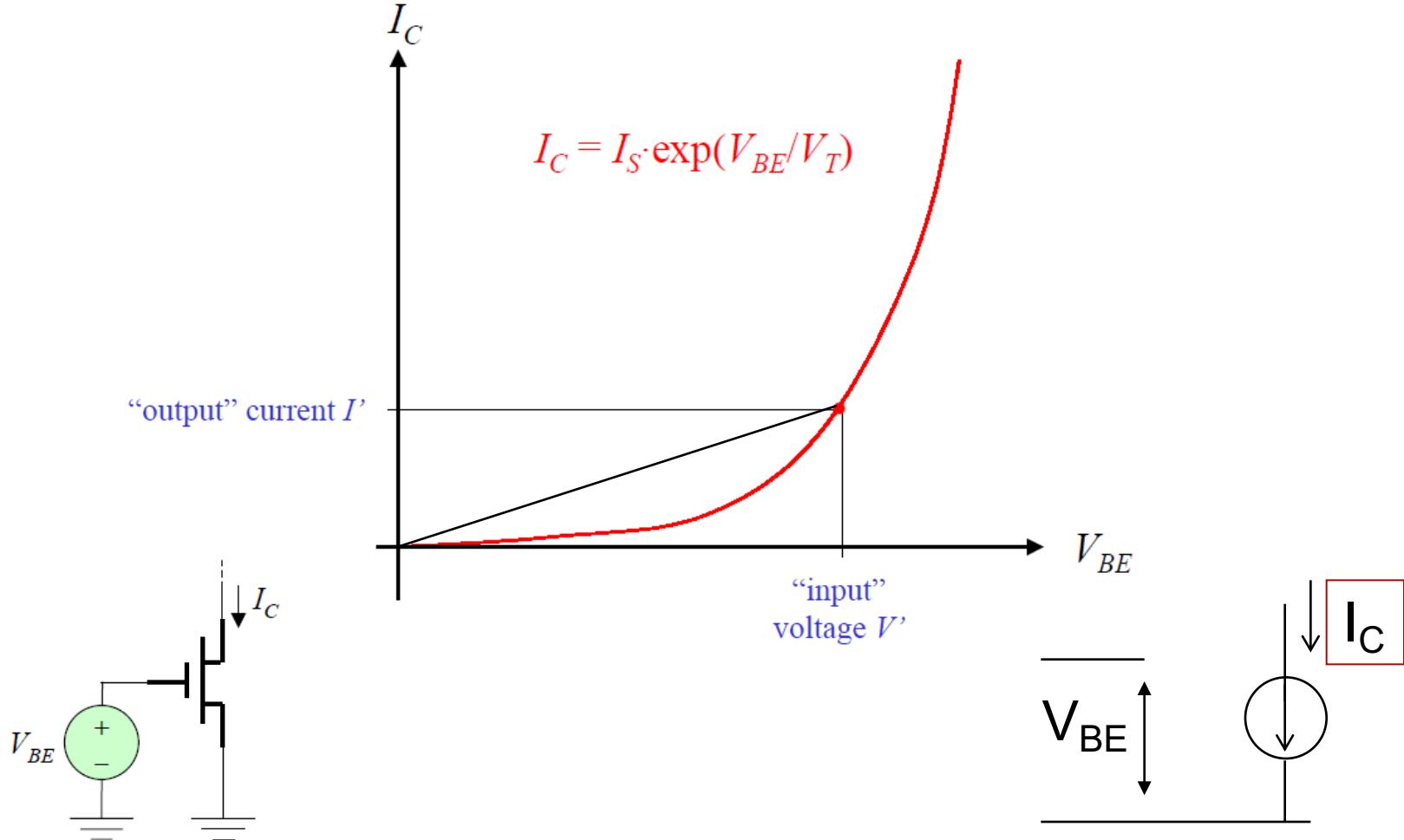
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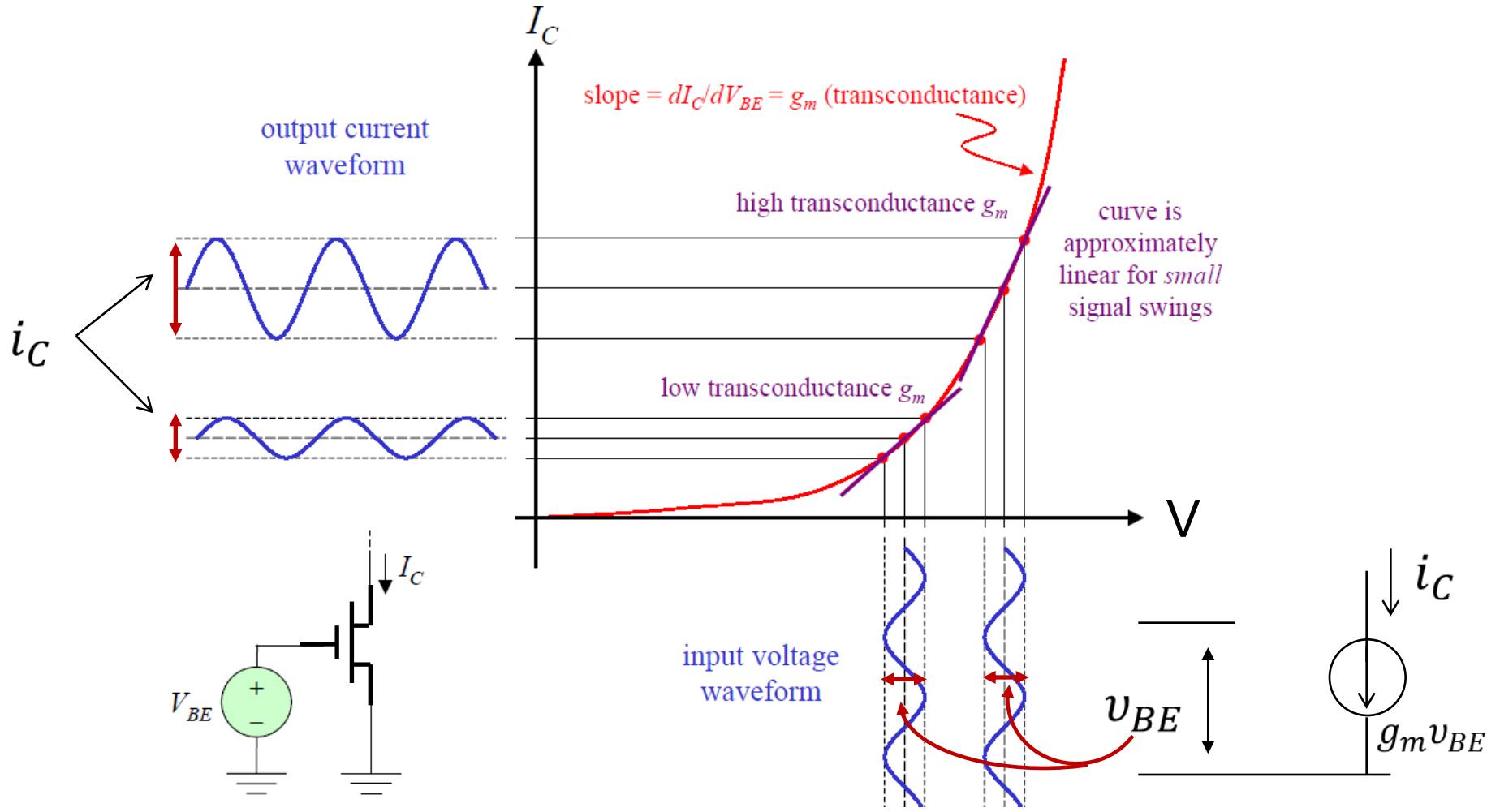
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$$I_d = \begin{cases} 0 & V_{gs} - V_T < 0 \\ \frac{1}{2} k_n (V_{gs} - V_T)^2 (1 + \lambda V_{ds}) & 0 \leq V_{gs} - V_T < V_{ds} \\ k_n [(V_{gs} - V_T) V_{ds} - \frac{1}{2} V_{ds}^2] & V_{gs} - V_T \geq V_{ds} \end{cases}$$



11.2 conductance and transconductance

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transconductance

$$g_n = \frac{dI_d}{dV_g} = k_n (V_{gs} - V_T) (1 + \lambda V_{ds}) = \frac{2I_d}{(V_{gs} - V_T)}$$

$$g_m = k_n (V_{gs} - V_T) (1 + \lambda V_{ds})$$



11.2 conductance and transconductance

$$I_d = \begin{cases} 0 & V_{gs} - V_T < 0 \\ \frac{1}{2} k_n (V_{gs} - V_T)^2 (1 + \lambda V_{ds}) & 0 \leq V_{gs} - V_T < V_{ds} \\ k_n [(V_{gs} - V_T) V_{ds} - \frac{1}{2} V_{ds}^2] & V_{gs} - V_T \geq V_{ds} \end{cases}$$

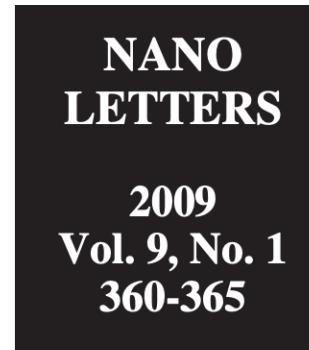
Output Impedance

$$\frac{1}{r_{on}} = \frac{dI_d}{dV_{ds}} = \lambda k_n (V_{gs} - V_T)^2 = \frac{\lambda I_d}{1 + \lambda V_{ds}}$$

$$g_m = k_n (V_{gs} - V_T) (1 + \lambda V_{ds})$$



How the knowledge used by engineers and scientists



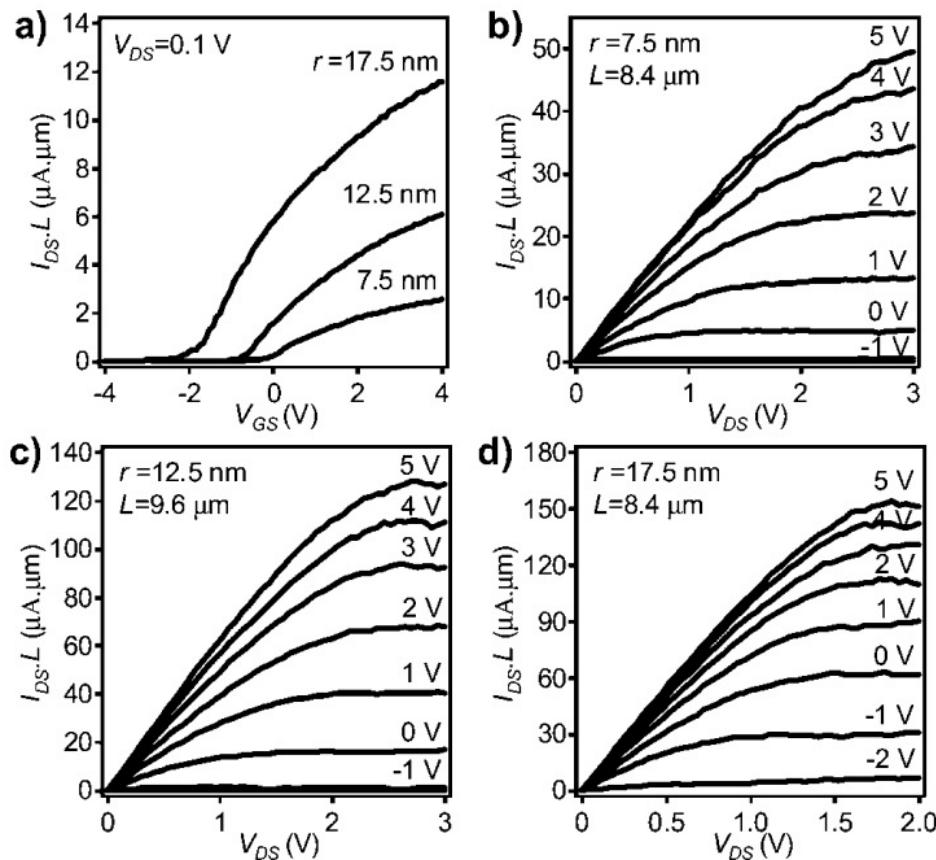
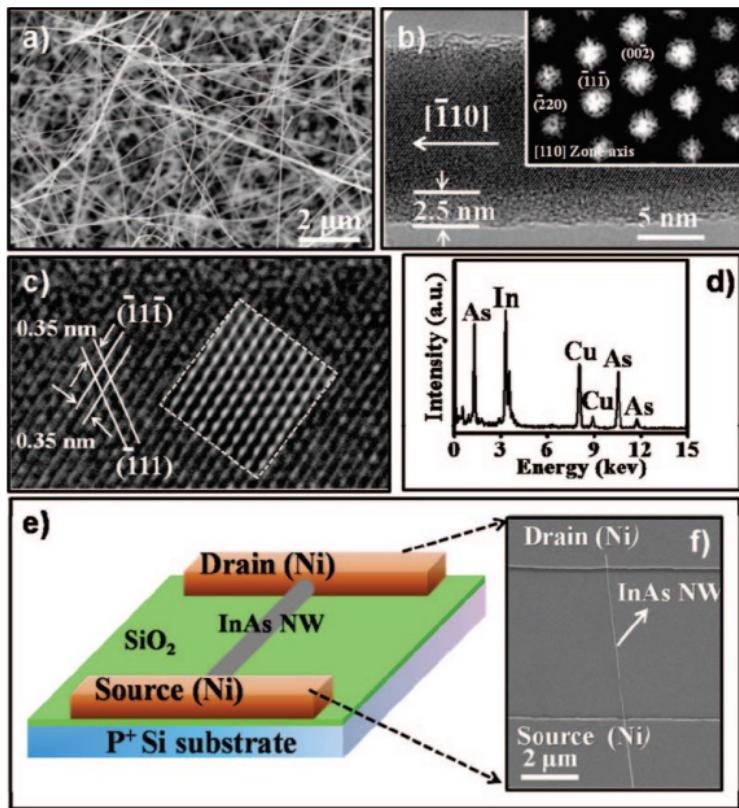
Diameter-Dependent Electron Mobility of InAs Nanowires

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Zhiyong Fan,^{‡,§,||} Jing Guo,[†] Jeffrey Bokor,^{‡,§} and Ali Javey^{*,†,§,||}

Department of Electrical Engineering and Computer Sciences, University of California at Berkeley, Berkeley, California 94720, Materials Sciences Division, Lawrence Berkeley National Laboratory, Berkeley, California 94720, Berkeley Sensor and Actuator Center, University of California at Berkeley, Berkeley, California 94720, and Department of Electrical and Computer Engineering, University of Florida, Gainesville, Florida 32611



How the knowledge used by engineers and scientists



How the knowledge used by engineers and scientists

We next assess the field-effect electron mobility of InAs NW FETs by using the low-bias ($V_{DS} = 0.1$ V) transconductance

$$g_m = \frac{dI_{DS}}{dV_{GS}} \Big|_{V_{DS}}$$

and the analytical expression

$$\mu_n = g_m \frac{L^2}{C_{ox}} \frac{1}{V_{DS}}$$

total

For classical transistor

$$g_m = \mu_n C_{ox} \frac{W}{L} V_{ds}$$

MOSFETs. The field-effect and effective mobilities are, however, deduced from the $I-V$ characteristics by using different analytical models. Specifically, the effective mobility is deduced from the drain conductance

$$g_D = \frac{dI_{DS}}{dV_{DS}} \Big|_{V_{GS}}$$

with

$$\mu_{n,eff} = g_D \frac{L^2}{C_{ox}} \frac{1}{(V_{GS} - V_t)}$$

total

For classical transistor

$$g_D = \mu_n C_{ox} \frac{W}{L} (V_{gs} - V_T)$$

Per unit area



Check your understanding

Problem example 2

The transconductance of an n-channel MOSFET is found to be $g_m = \partial I_D / \partial V_{GS} = 1.25 \text{ mA/V}$ when measured at $V_{DS} = 50 \text{ mV}$. The threshold voltage is $V_T = 0.3 \text{ V}$.

- (a) Determine the conductance parameter K_n . (b) What is the current at $V_{GS} = 0.8 \text{ V}$ and $V_{DS} = 50 \text{ mV}$? (c) Determine the current at $V_{GS} = 0.8 \text{ V}$ and $V_{DS} = 1.5 \text{ V}$.



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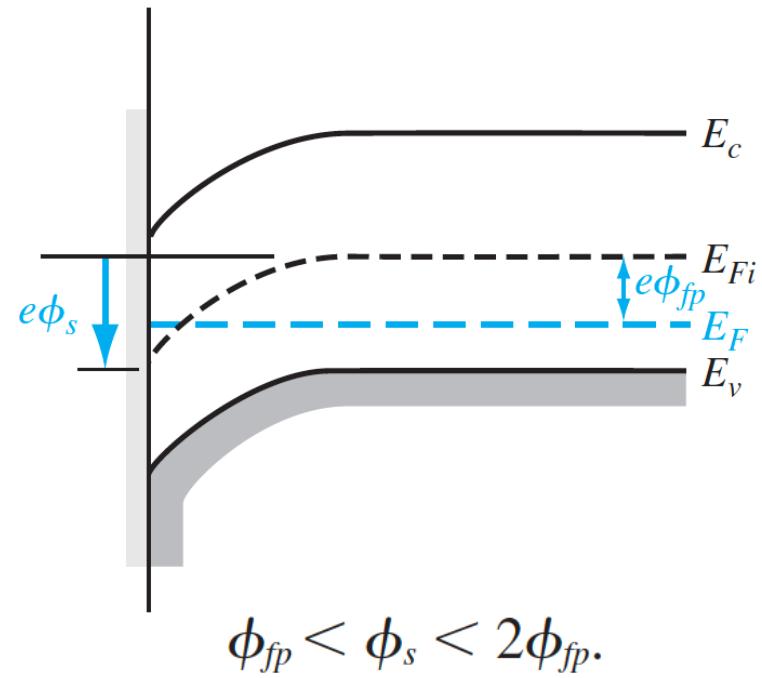
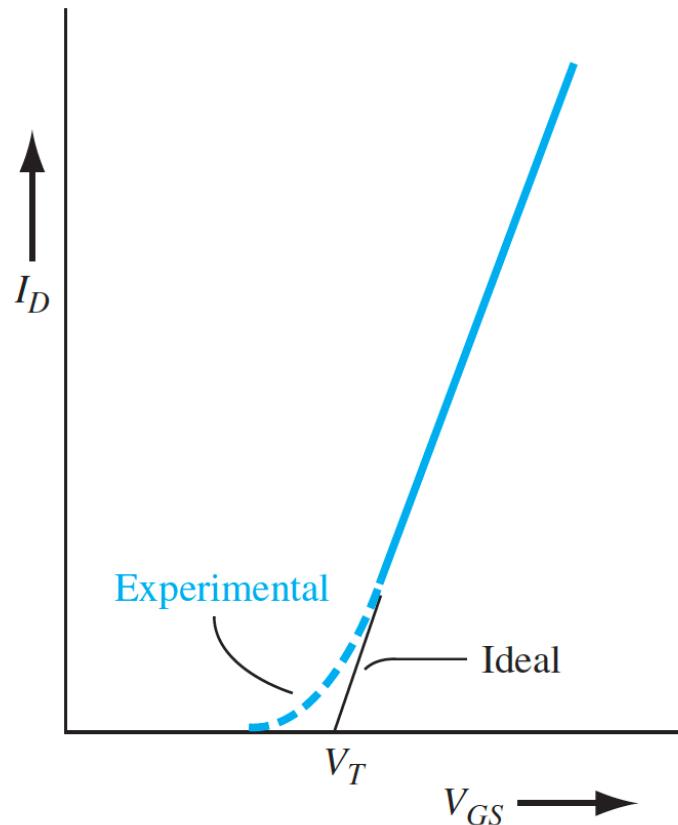
11.4 Velocity Saturation

11.5 Short Channel Effect

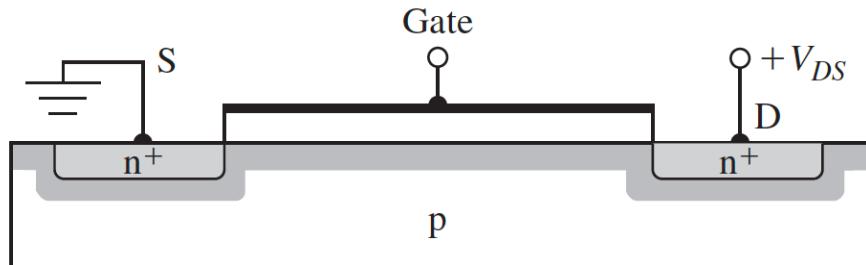


11.3 Subthreshold conduction

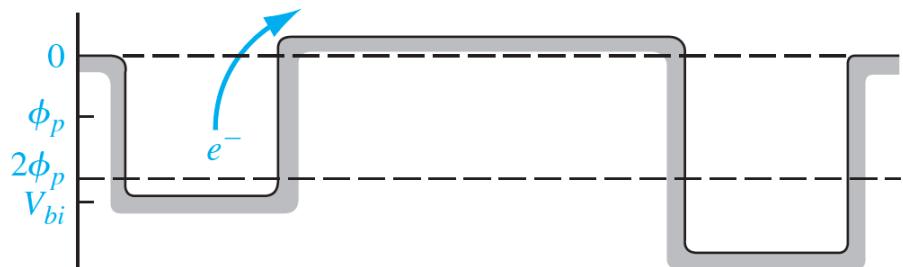
$$V_{GS} < V_T$$



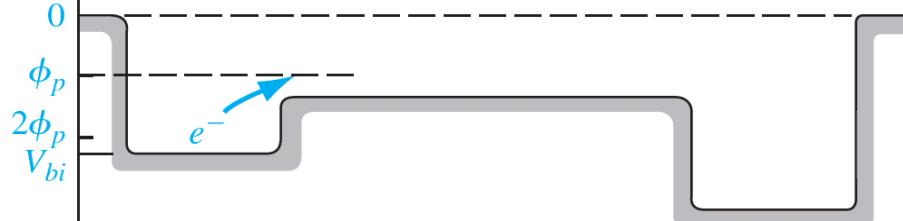
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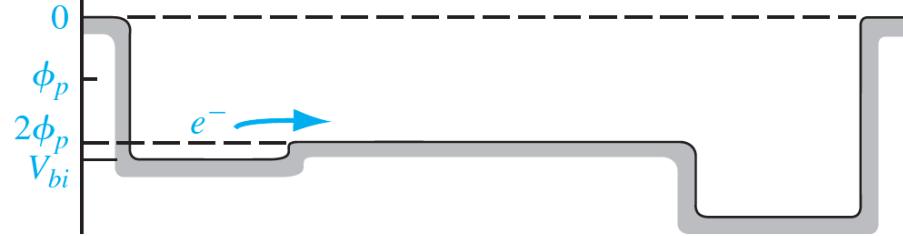
Accumulation



Weak inversion



Inversion



11.3 Subthreshold conduction

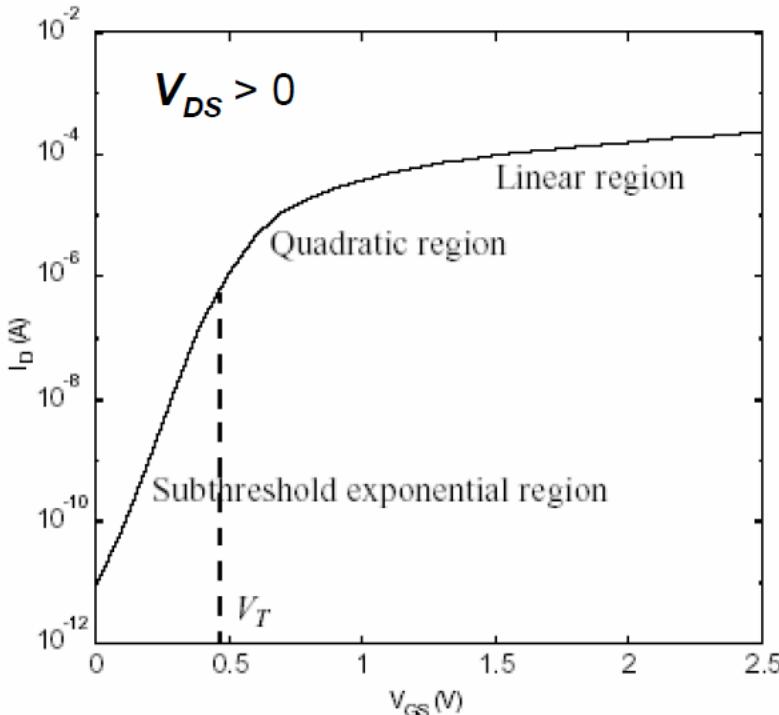
Subthreshold Conduction (Leakage Current)

- The transition from the ON state to the OFF state is gradual. This can be seen more clearly when I_D is plotted on a logarithmic scale:
- In the subthreshold ($V_{GS} < V_T$) region,

$$I_D \propto \exp\left(\frac{qV_{GS}}{nkT}\right)$$

This is essentially the channel-source pn junction current.

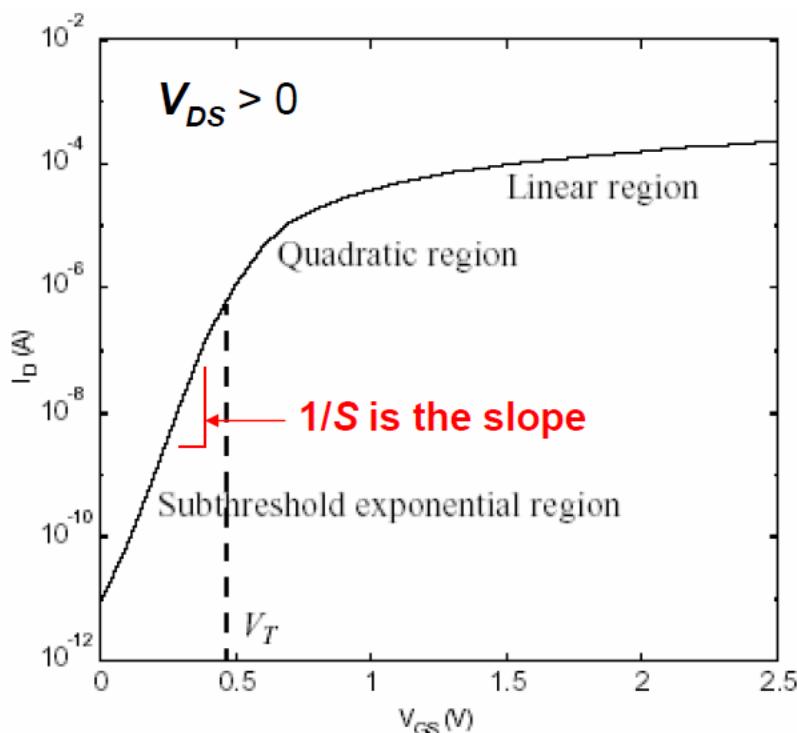
(Some electrons diffuse from the source into the channel, if this pn junction is forward biased.)



11.3 Subthreshold conduction

Slope Factor (or Subthreshold Swing) S

- S is defined to be the inverse slope of the log (I_D) vs. V_{GS} characteristic in the subthreshold region:



$$S \equiv n \left(\frac{kT}{q} \right) \ln(10)$$

Units: Volts per decade

Note that $S \geq 60 \text{ mV/dec}$ at room temperature:

$$\left(\frac{kT}{q} \right) \ln(10) = 60 \text{ mV}$$

11.3 Subthreshold conduction

V_T Design Trade-Off

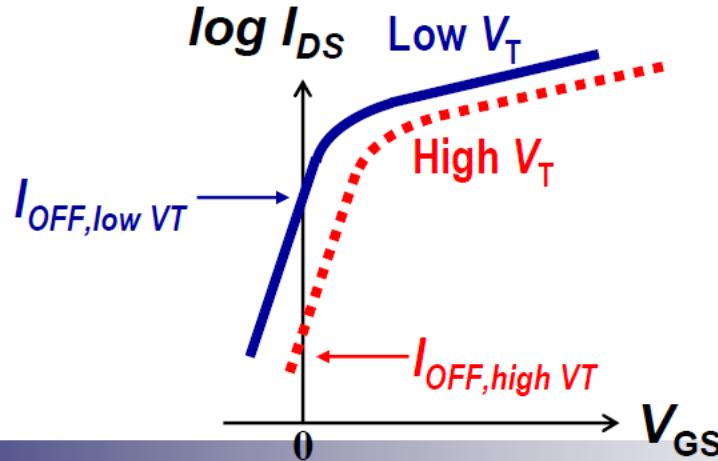
(Important consideration for digital-circuit applications)

- Low V_T is desirable for high ON current

$$I_{DSAT} \propto (V_{DD} - V_T)^\eta \quad 1 < \eta < 2$$

where V_{DD} is the power-supply voltage

...but high V_T is needed for low OFF current



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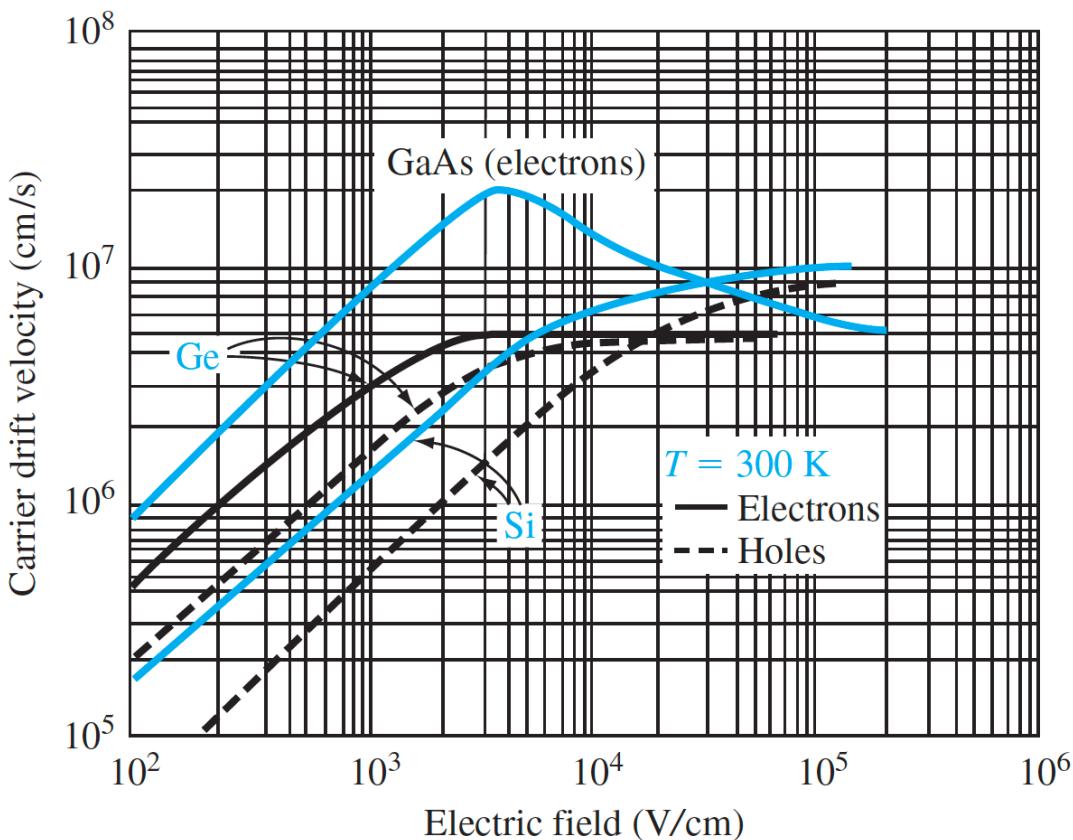
11.5 Short Channel Effect



11.4 Velocity Saturation

$$v_d \rightarrow v_{th}$$

- Electric field is heating up electrons
- Electrons transfer energy to lattice to reach thermal equilibrium



$$v_n = \frac{v_s}{\left[1 + \left(\frac{E_{on}}{E} \right)^2 \right]^{1/2}}$$

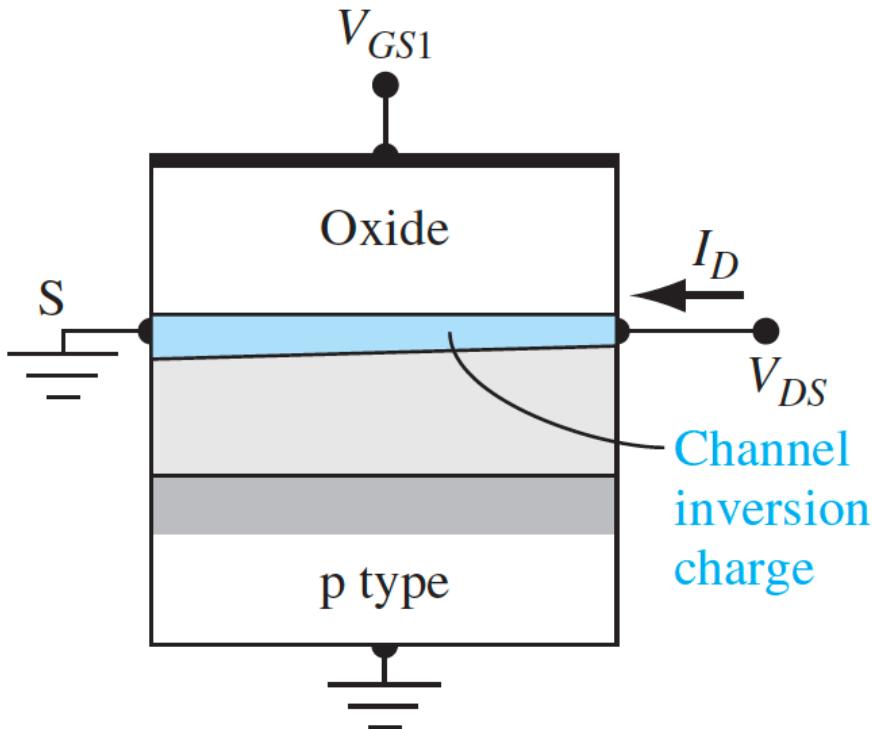
$$v_p = \frac{v_s}{\left[1 + \left(\frac{E_{op}}{E} \right)^2 \right]^{1/2}}$$

Probably a typo in textbook

11.4 Velocity Saturation

$$v_d \rightarrow v_{th}$$

- Electric field is heating up electrons
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$$E_{DS} = \frac{V_{DS}}{L}$$

As the transistor size scales down, the electric field intensity E increases.

$$E_{on} = \frac{V_{DSAT}}{L}$$

11.4 Velocity Saturation

$$v_d \rightarrow v_{th}$$

As the transistor size scales down,
the electric field intensity E increases.

- Electric field is heating up electrons
- Electrons transfer energy to lattice to reach thermal equilibrium

$$\begin{aligned} I_{DSAT} &= \mu_n C_{ox} \frac{W}{L} \left(V_{GS} - VT - \frac{1}{2} V_{DS} \right) V_{DS} \\ &= C_{ox} W \left(V_{GS} - VT - \frac{1}{2} V_{DSAT} \right) \frac{V_{DSAT}}{L} \mu_n \end{aligned}$$

$$I_{DSAT} = WC_{ox} \left[V_{GS} - V_T - \frac{V_{DSAT}}{2} \right] v_{sat}$$

$$\text{where } V_{DSAT} = \frac{L}{\mu_n} v_{sat}$$



11.4 Velocity Saturation

Unified model

$$I_D = 0 \text{ for } V_{GT} \leq 0$$

$$I_D = k' \frac{W}{L} \left(V_{GT} V_{min} - \frac{V_{min}^2}{2} \right) \quad \text{for } V_{GT} \geq 0$$

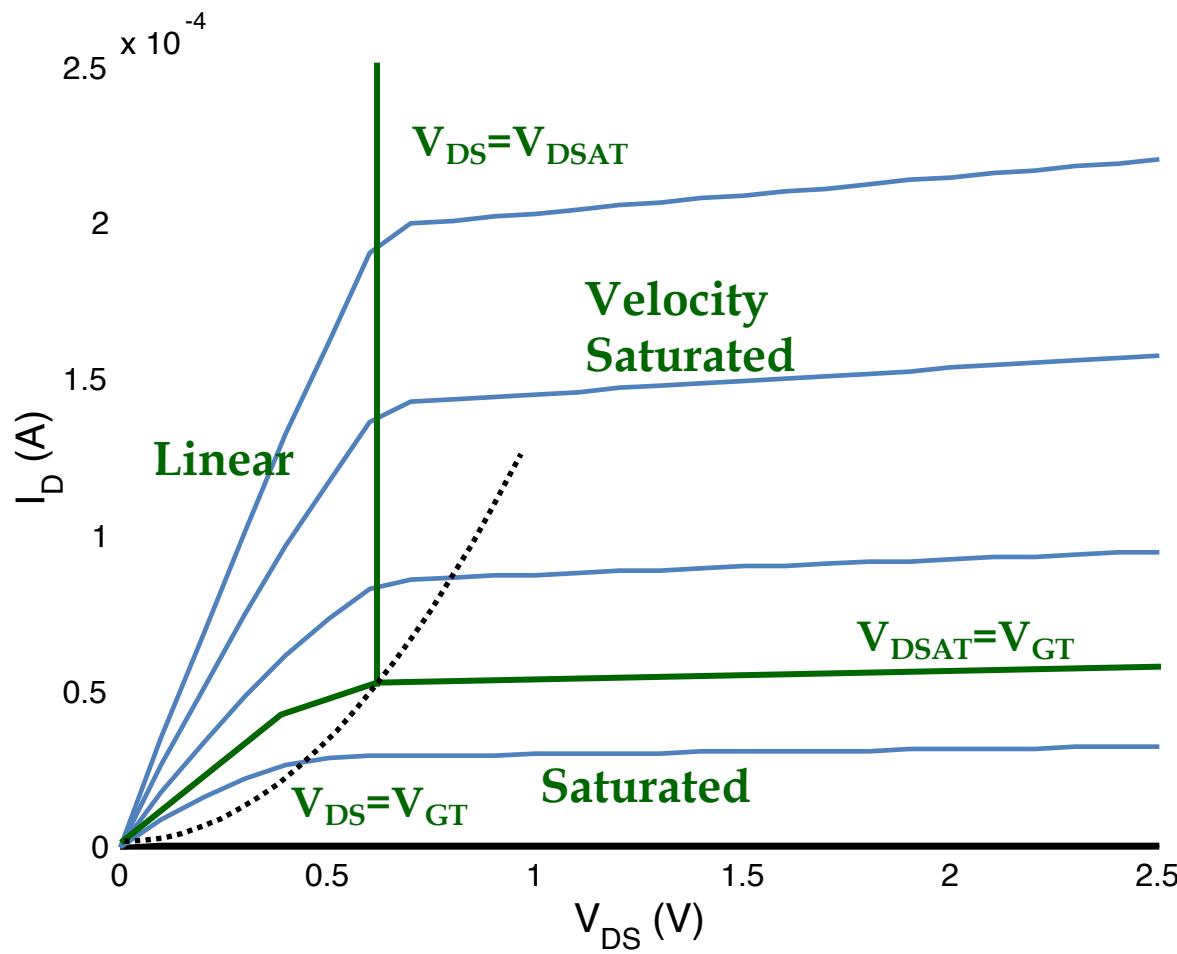
with $V_{min} = \min(V_{GT}, V_{DS}, V_{DSAT})$,

$$V_{GT} = V_{GS} - V_T,$$

$$\text{and } V_T = V_{T0} + \gamma (\sqrt{-2\phi_F + V_{SB}} - \sqrt{-2\phi_F})$$

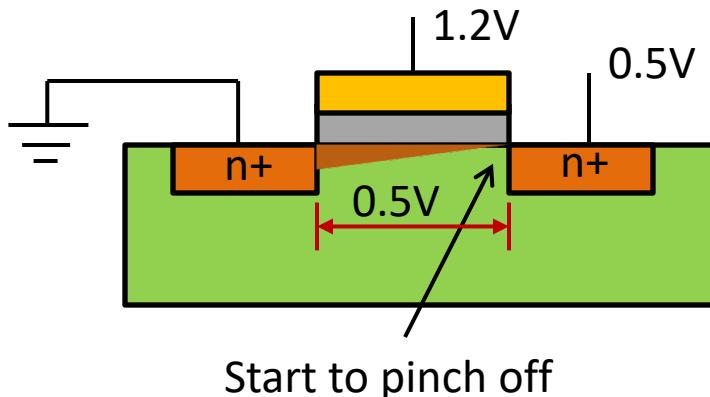


11.4 Velocity Saturation



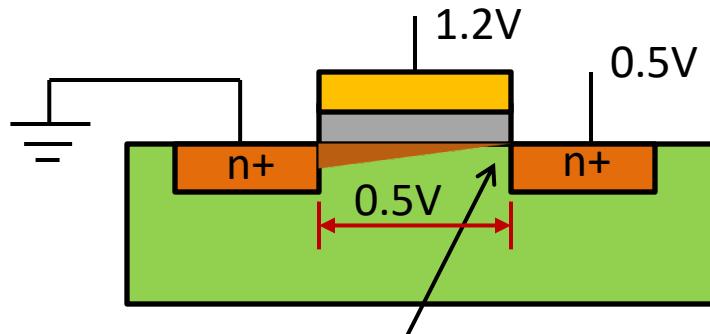
Example

$$V_T = 0.7 \text{ , } V_{gs} = 1.2 \text{ V, } V_{sat} = 1 \text{ V}$$

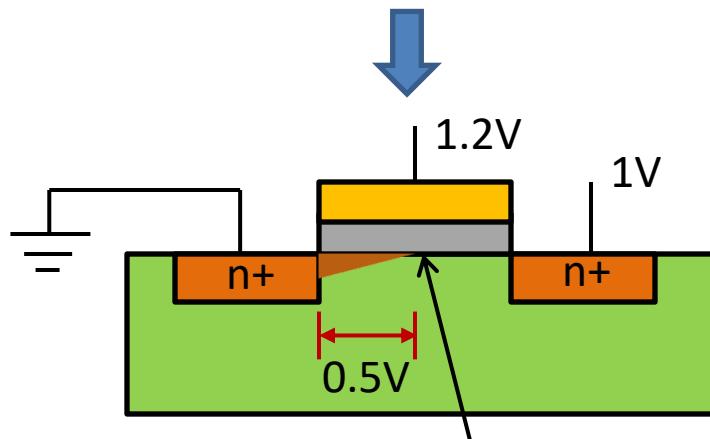


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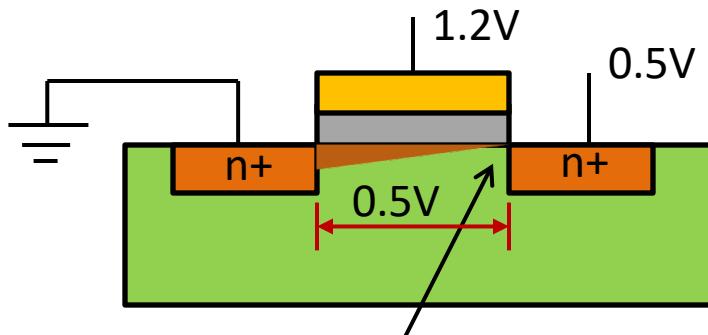
Start to pinch off



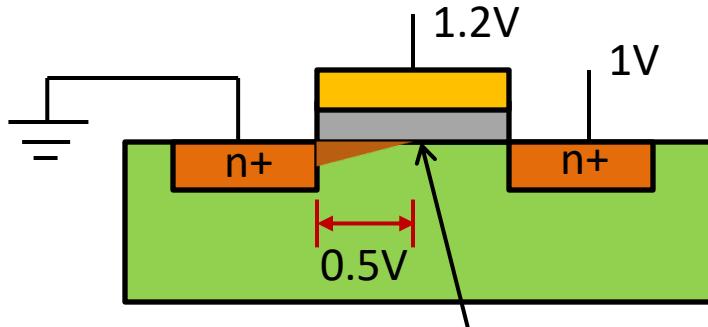
Start to pinch off

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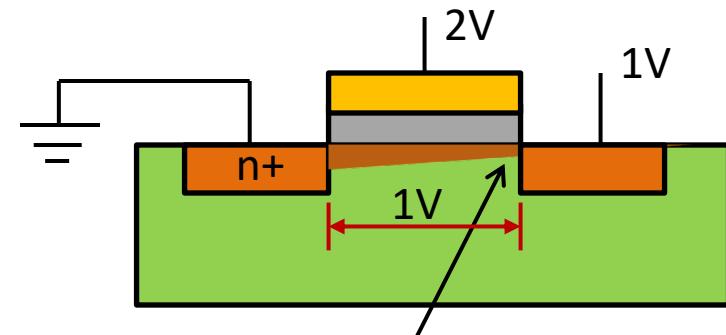
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Start to pinch off



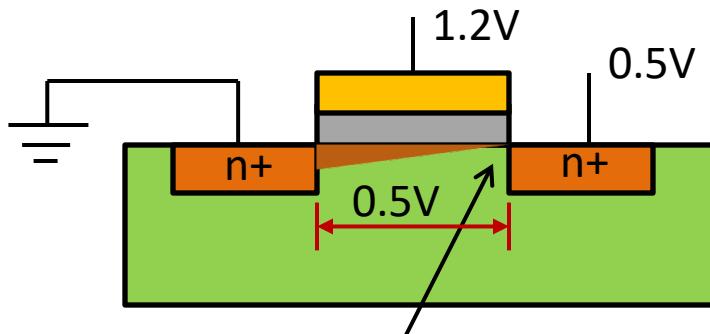
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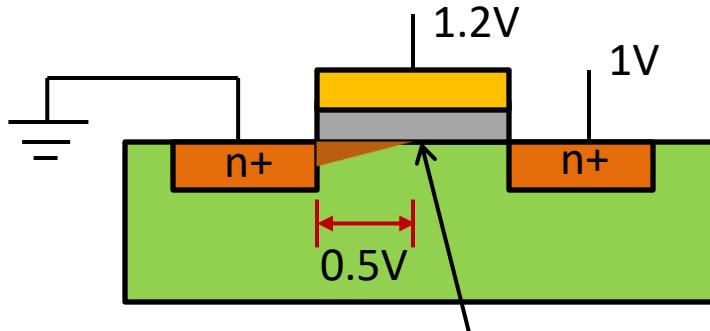
- NO pinch off
- Velocity saturation starts

Example

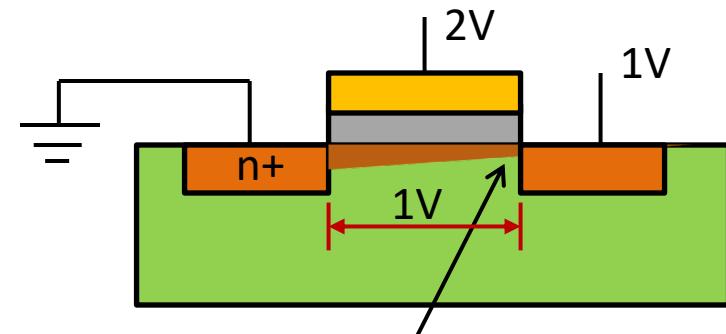
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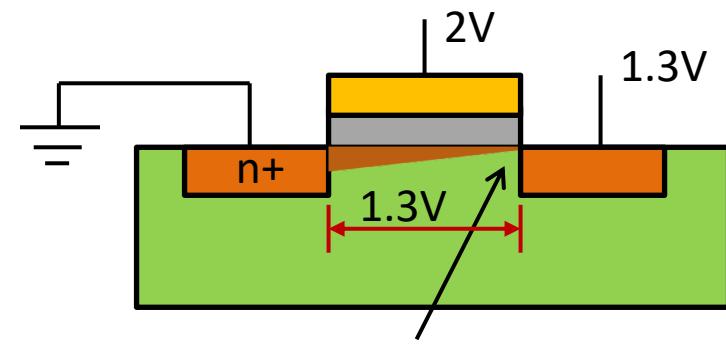
Start to pinch off



Start to pinch off



- NO pinch off
- Velocity saturation starts



- Starts to pinch off
- Velocity saturation

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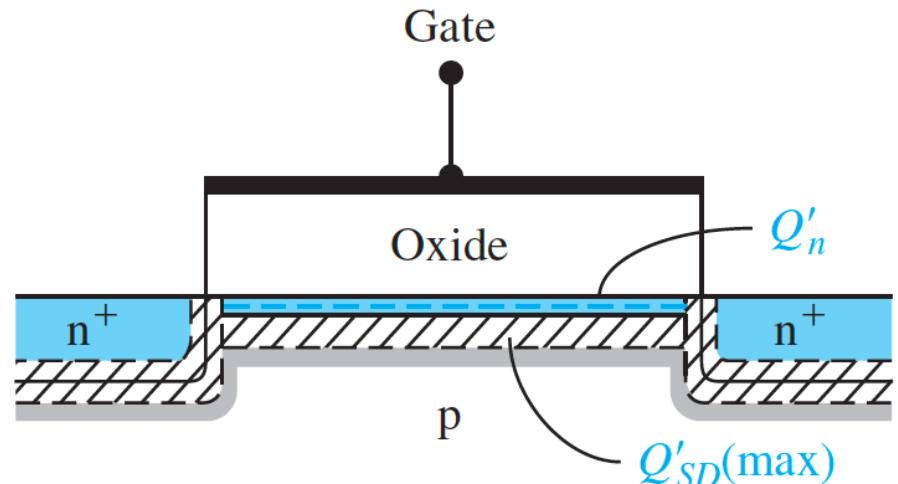
11.3 Subthreshold conduction

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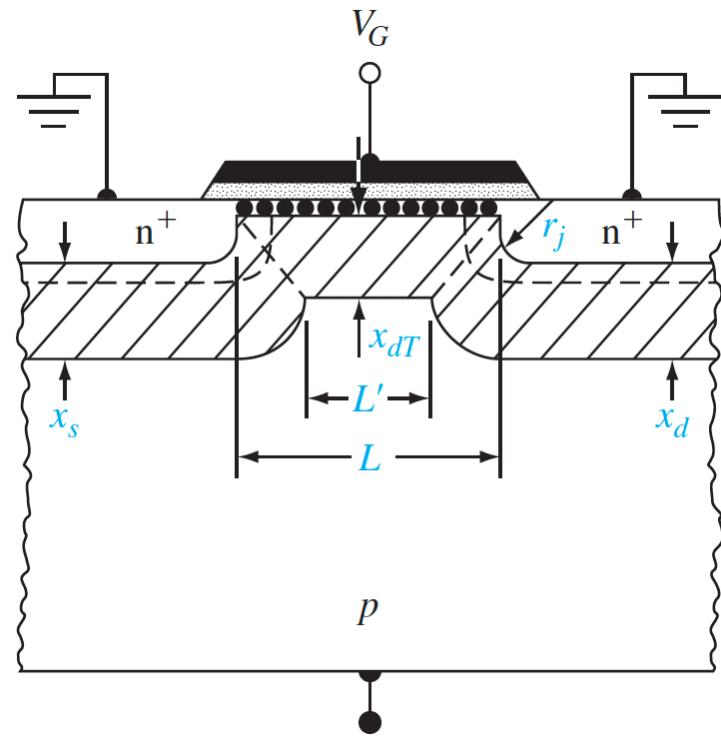
11.5 Short Channel Effect



11.5 Short Channel Effect



A long channel device



A short channel device

11.5 Short Channel Effect

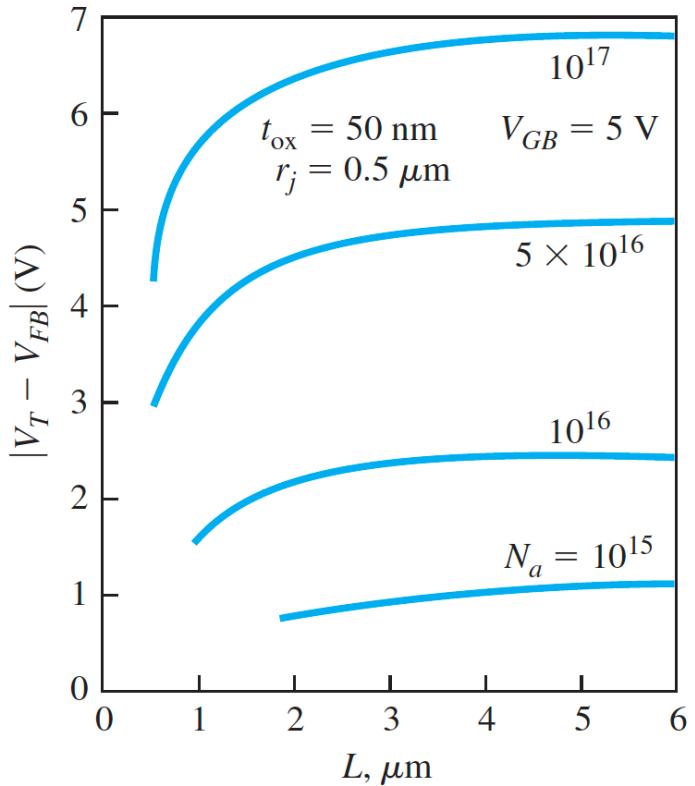


Figure 11.16 | Threshold voltage versus channel length for various substrate dopings.
(From Yau [26].)

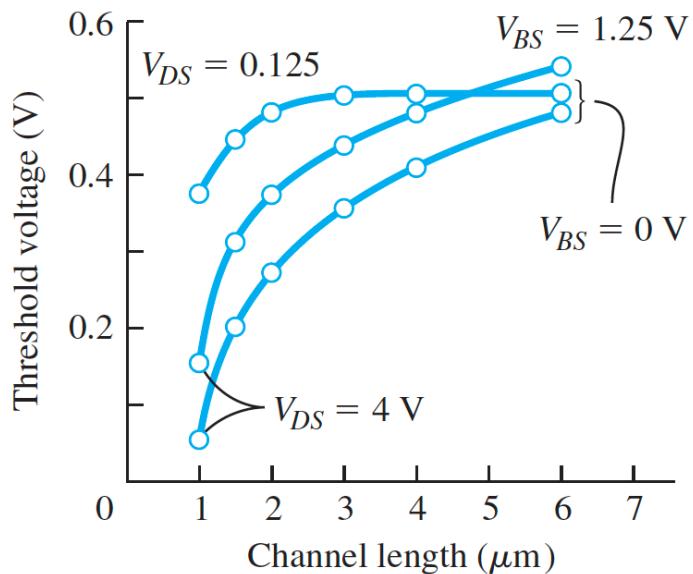


Figure 11.17 | Threshold voltage versus channel length for two values of drain-to-source and body-to-source voltage.
(From Yang [25].)